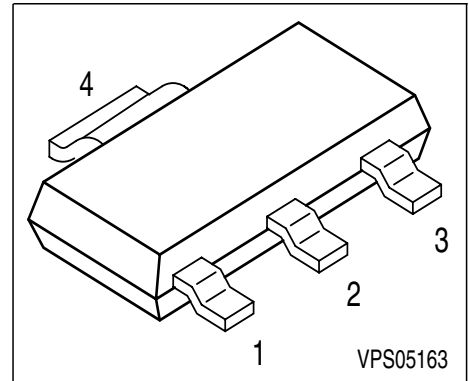


NPN Silicon RF Transistor

- For low-distortion broadband output amplifier stages in antenna and telecommunication systems up to 2 GHz at collector currents from 120 mA to 250 mA
- Power amplifiers for DECT and PCN systems
- Integrated emitter ballast resistor
- $f_T = 5.5$ GHz



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration				Package
BFG 235	BFG235	1 = E	2 = B	3 = E	4 = C	SOT-223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	15	V
Collector-emitter voltage	V_{CES}	25	
Collector-base voltage	V_{CBO}	25	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	300	mA
Base current	I_B	40	
Total power dissipation, $T_S \leq 80$ °C F)	P_{tot}	2	W
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point	R_{thJS}	≤ 35	K/W
----------------------------	------------	-----------	-----

¹ T_S is measured on the collector lead at the soldering point to the pcb

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 25\text{ V}, V_{BE} = 0$	I_{CES}	-	-	200	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}, I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$	I_{EBO}	-	-	2	μA
DC current gain $I_C = 200\text{ mA}, V_{CE} = 8\text{ V}$	h_{FE}	50	120	250	-

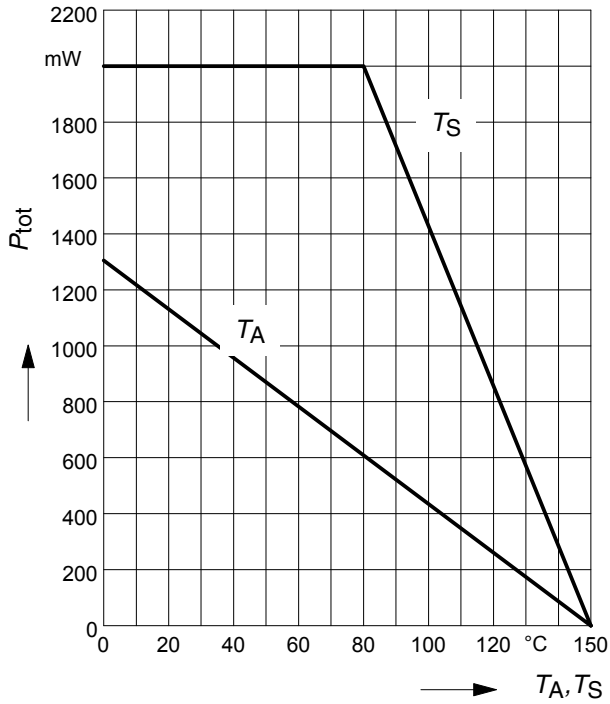
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC characteristics (verified by random sampling)					
Transition frequency $I_C = 200\text{ mA}, V_{CE} = 8\text{ V}, f = 200\text{ MHz}$	f_T	4	5.5	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	2.6	3.6	pF
Collector-emitter capacitance $V_{CE} = 10\text{ V}, f = 1\text{ MHz}$	C_{ce}	-	1.5	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	C_{eb}	-	15	-	
Noise figure $I_C = 60\text{ mA}, V_{CE} = 8\text{ V}, Z_S = Z_{Sopt}, f = 900\text{ MHz}$	F	-	2.7	-	dB
Power gain, maximum available ^{F)} $I_C = 200\text{ mA}, V_{CE} = 8\text{ V}, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 900\text{ MHz}$	G_{ma}	-	12	-	
Transducer gain $I_C = 200\text{ mA}, V_{CE} = 8\text{ V}, Z_S = Z_L = 50\Omega, f = 900\text{ MHz}$	$ S_{21e} ^2$	-	6	-	
Third order intercept point $I_C = 200\text{ mA}, V_{CE} = 8\text{ V}, Z_S = Z_L = 50\Omega, f = 900\text{ MHz}$	IP_3	-	40	-	dBm

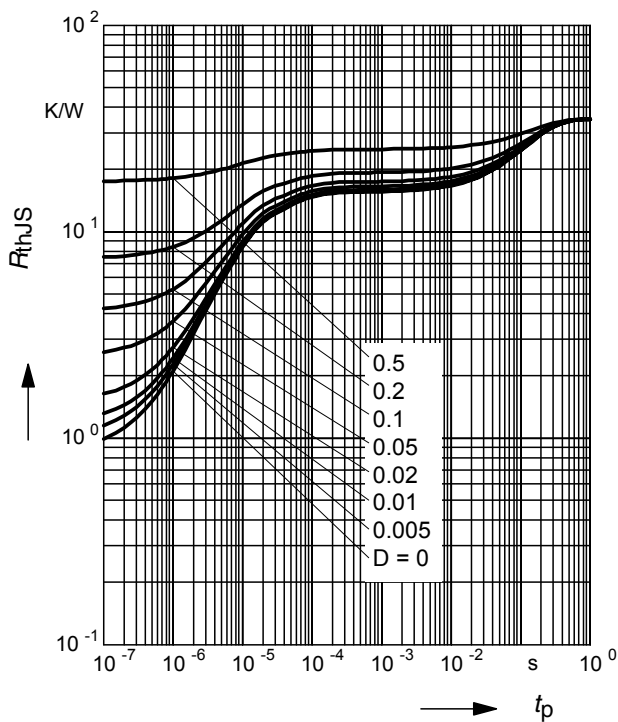
$$^1G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

Total power dissipation $P_{tot} = f(T_A^*, T_S)$

* Package mounted on epoxy

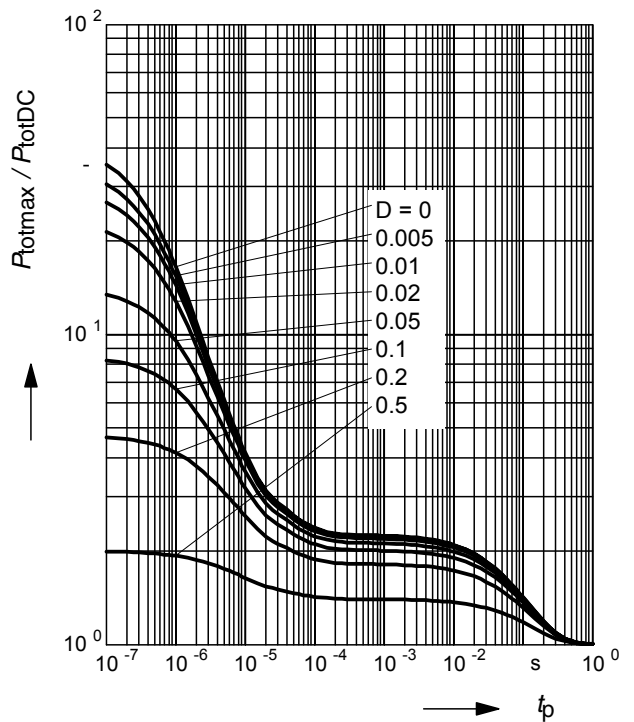


Permissible Pulse Load $R_{thJS} = f(t_p)$



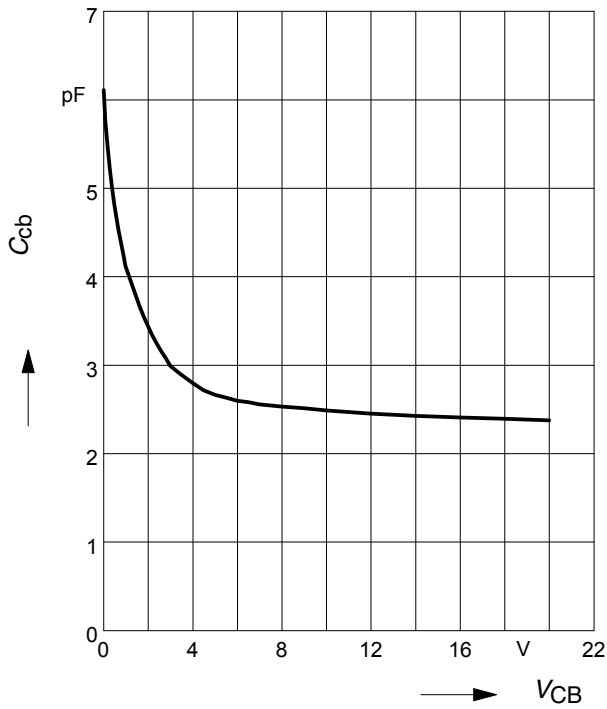
Permissible Pulse Load

$P_{totmax} / P_{totDC} = f(t_p)$



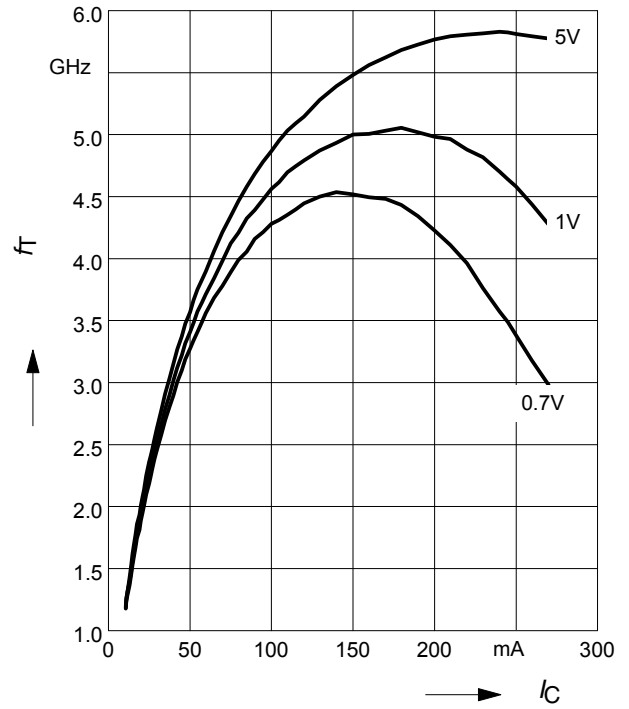
Collector-base capacitance $C_{cb} = f(V_{CB})$

$f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

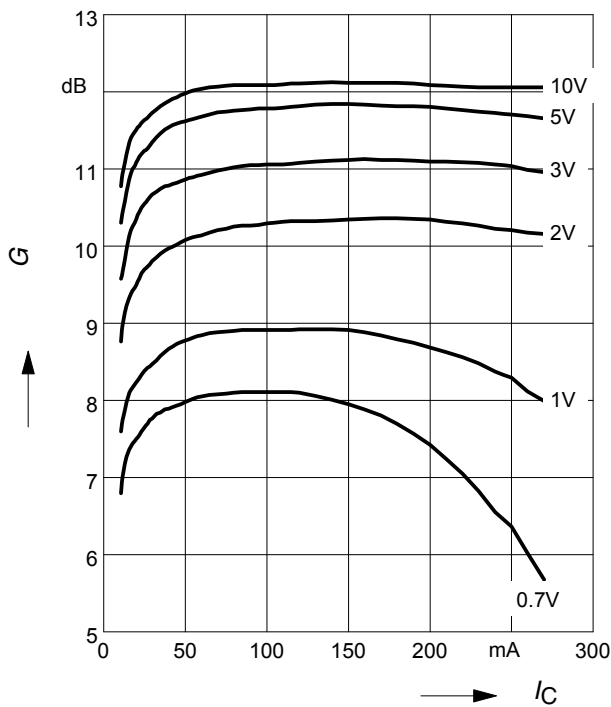
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

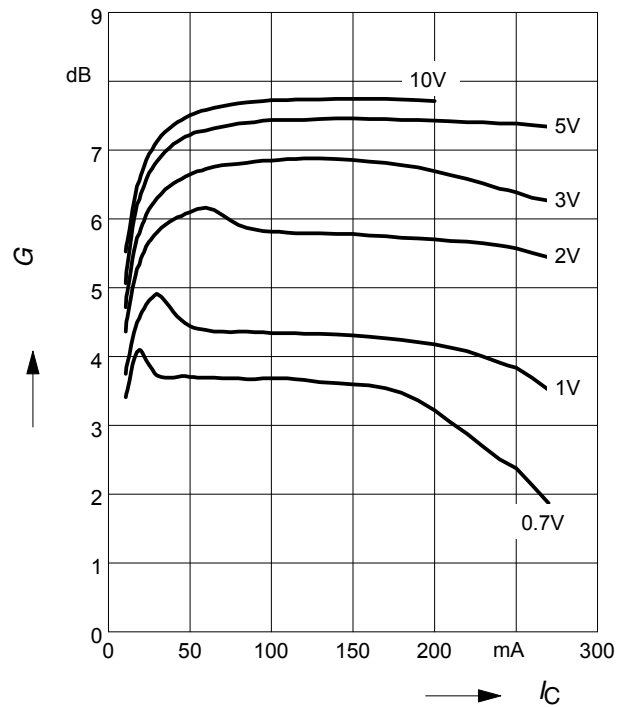
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 1.8\text{GHz}$

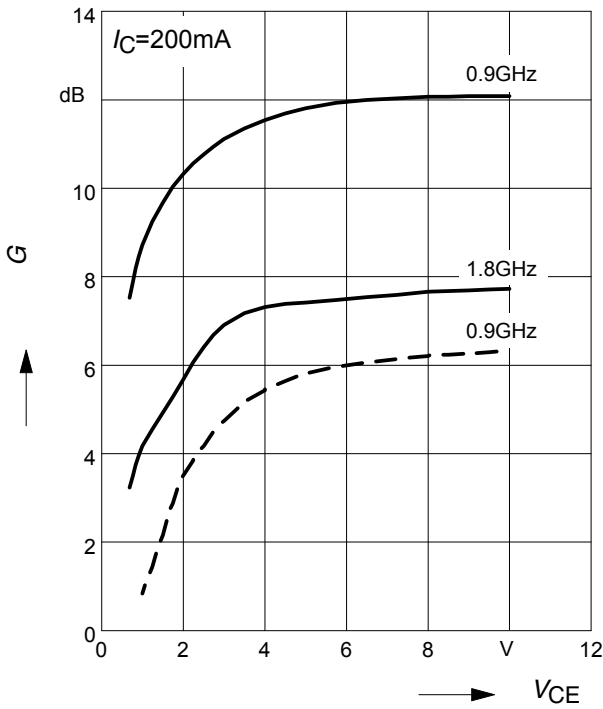
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(V_{CE})$: _____

$|S_{21}|^2 = f(V_{CE})$: -----

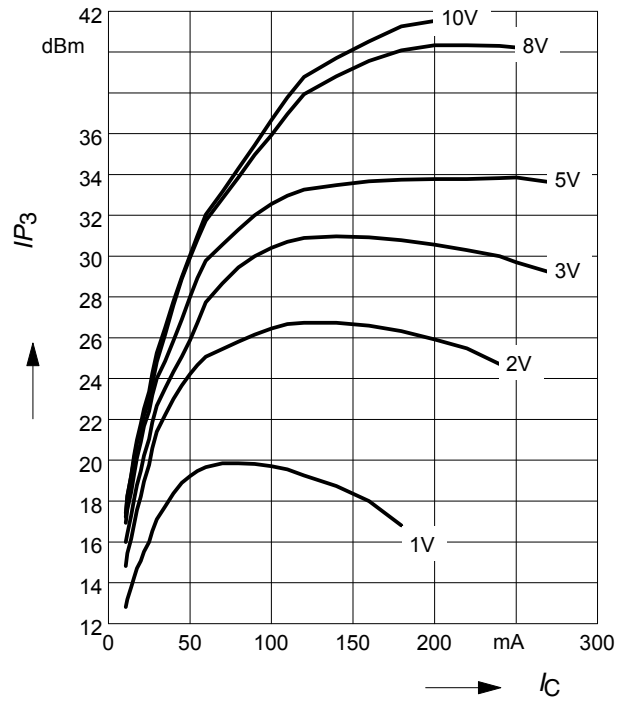
f = Parameter



Intermodulation Intercept Point $IP_3 = f(I_C)$

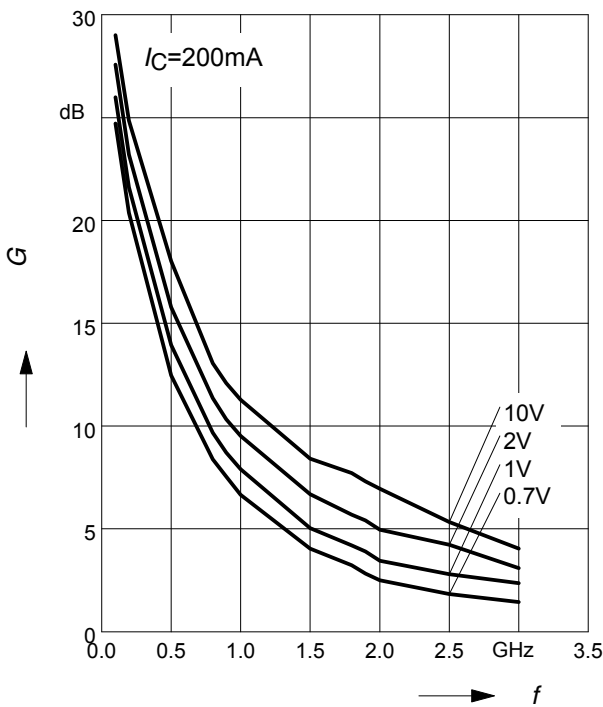
(3rd order, Output, $Z_S = Z_L = 50\Omega$)

V_{CE} = Parameter, $f = 900\text{MHz}$



Power Gain $G_{ma}, G_{ms} = f(f)$

V_{CE} = Parameter



Power Gain $|S_{21}|^2 = f(f)$

V_{CE} = Parameter

